

MT86N10N5

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- $V_{DS} = 60V$
- $I_D = 50A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} = 10\text{ m}\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} = 14\text{ m}\Omega$ @ $V_{GS} = 4.5V$

Features

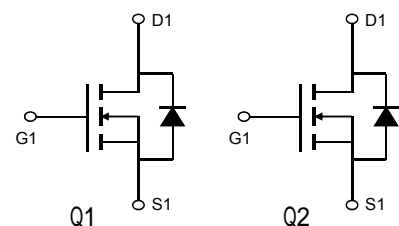
- Advanced Trench Process Technology.
- High Density Cell Design for Ultra Low On-Resistance.
- Lead free product is acquired.
- RoHS Compliant.
- PDFN5x6-8L Package



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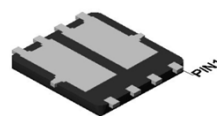
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Simplified Schematic

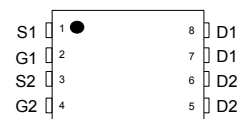


MARKING DIAGRAM & PIN ASSIGNMENT

DFN5X6-8L



Top View



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	60	V
V_{GS}	Gate to Source Voltage (Note 4)	± 25	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	20	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	50	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	22	
	-Pulsed	90	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	28	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	26	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} =$	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		14		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.0		2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		-6		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$		10	19	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$		14	23	
		$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		16	28	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 12\text{ A}$		45		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 45\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1011	1220	pF
C_{oss}	Output Capacitance			330	401	pF
C_{rss}	Reverse Transfer Capacitance			40	48	pF
R_g	Gate Resistance		0.2	1.0	2.0	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 45\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		9	18	ns
t_r	Rise Time			2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			15	31	ns
t_f	Fall Time			2	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	$V_{DD} = 15\text{ V}$, $I_D = 12\text{ A}$	16	26	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 5 V		8	11	nC
Q_{gs}	Gate to Source Charge			3.5		nC
Q_{gd}	Gate to Drain "Miller" Charge			1.9		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 1.9\text{ A}$ (Note 2)		0.75	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 12\text{ A}$ (Note 2)		0.80	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		26	41	ns
Q_{rr}	Reverse Recovery Charge			9	18	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $53\text{ }^{\circ}\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz. copper.



b. $125\text{ }^{\circ}\text{C/W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width $< 300\text{ }\mu\text{s}$, Duty cycle $< 2.0\%$.

3. E_{AS} of 21 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 0.3\text{ mH}$, $I_{AS} = 12\text{ A}$, $V_{DD} = 27\text{ V}$, $V_{GS} = 10\text{ V}$.

4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

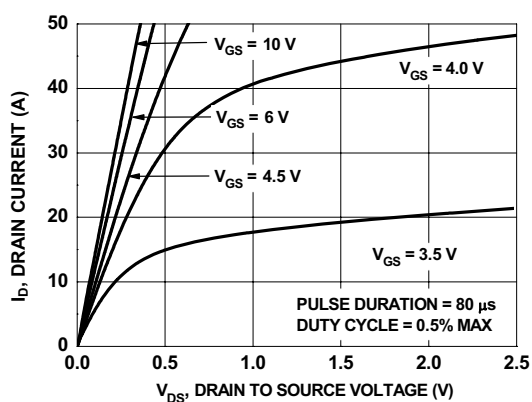


Figure 1. On Region Characteristics

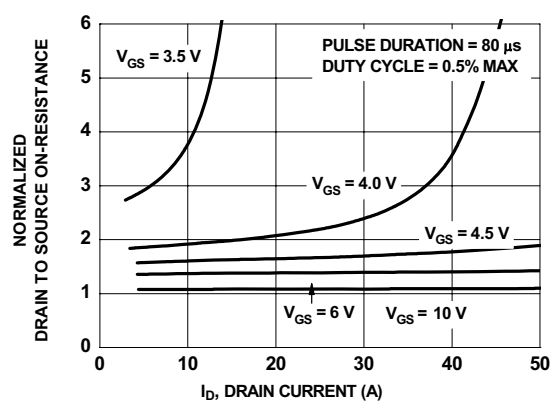


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

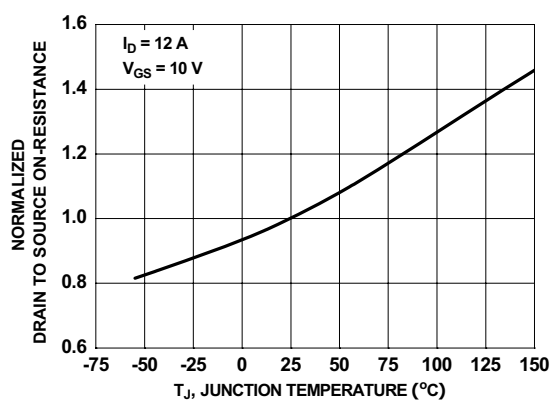


Figure 3. Normalized On Resistance vs Junction Temperature

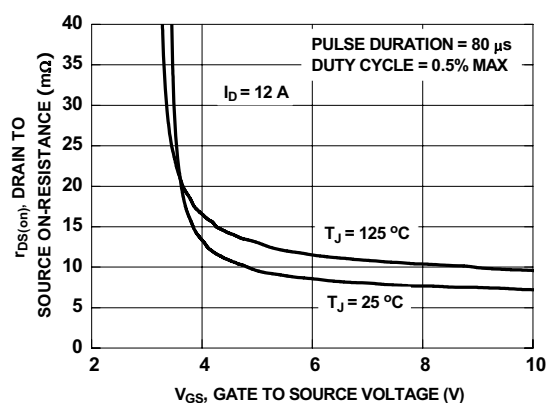


Figure 4. On-Resistance vs Gate to Source Voltage

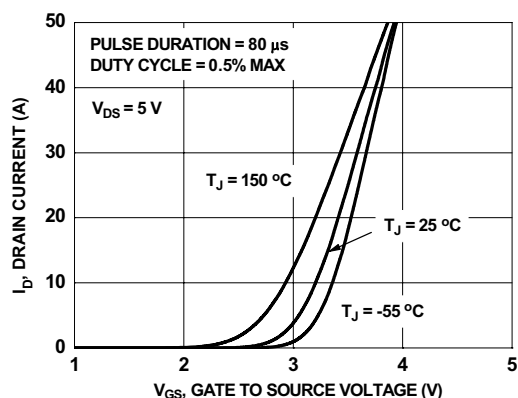


Figure 5. Transfer Characteristics

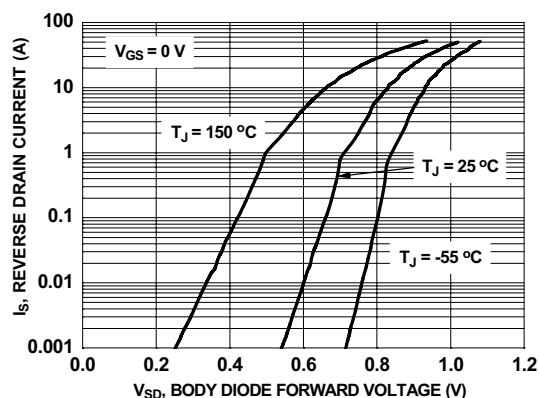


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

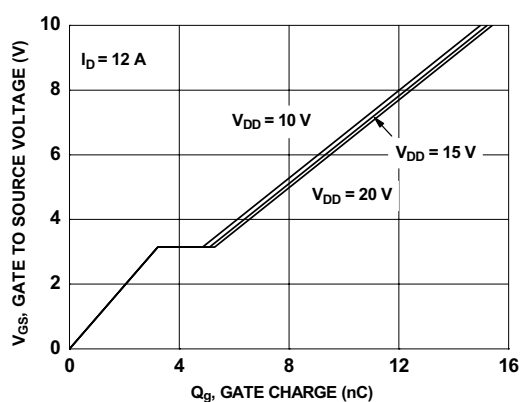


Figure 7. Gate Charge Characteristics

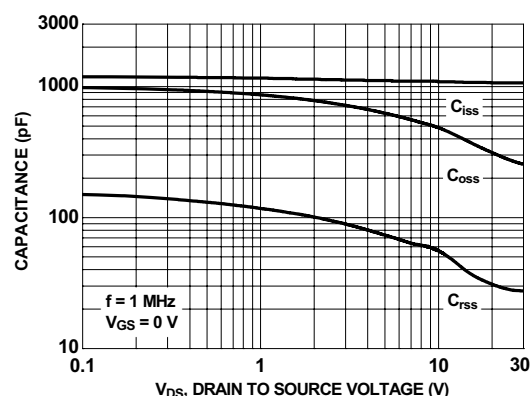


Figure 8. Capacitance vs Drain to Source Voltage

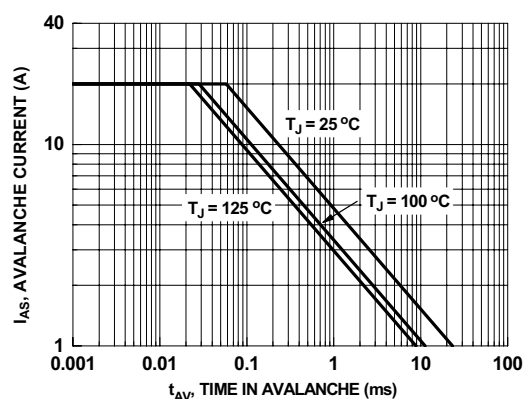


Figure 9. Unclamped Inductive Switching Capability

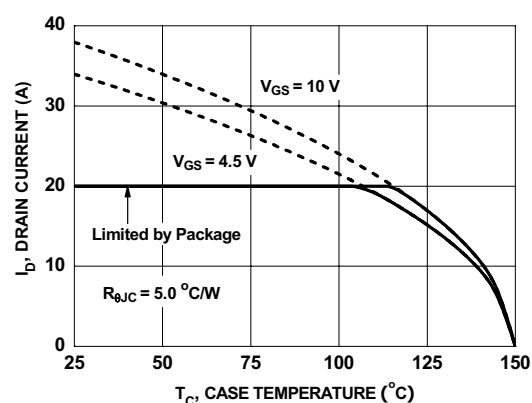


Figure 10. Maximum Continuous Drain Current vs Case Temperature

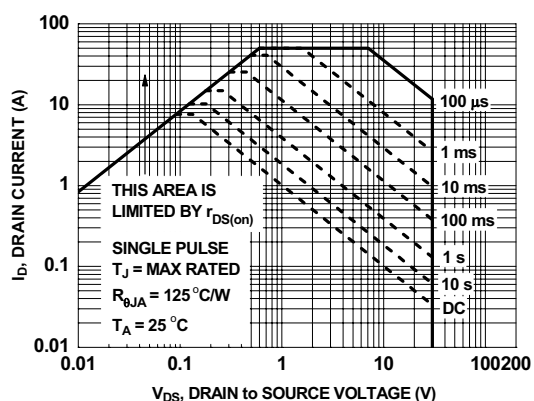


Figure 11. Forward Bias Safe Operating Area

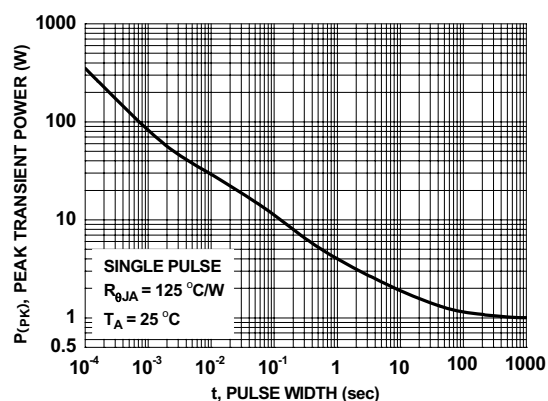
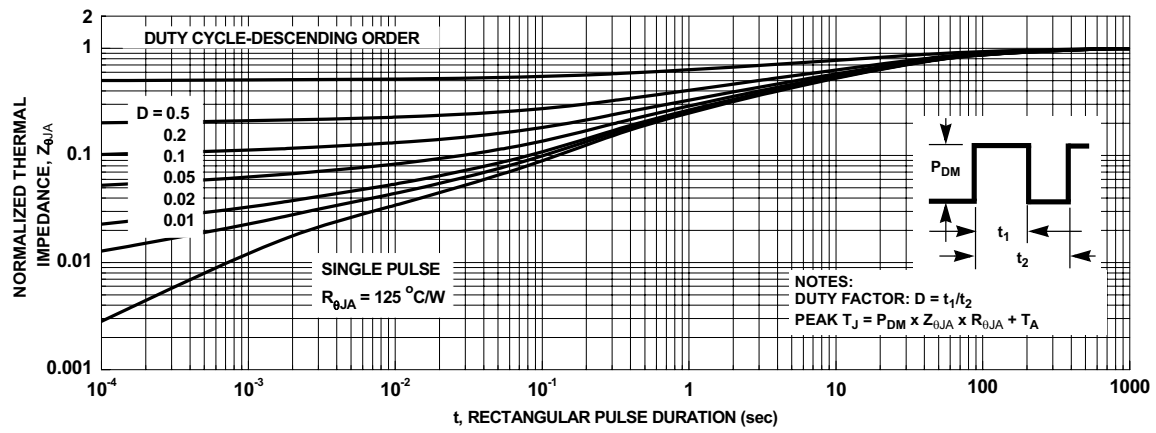
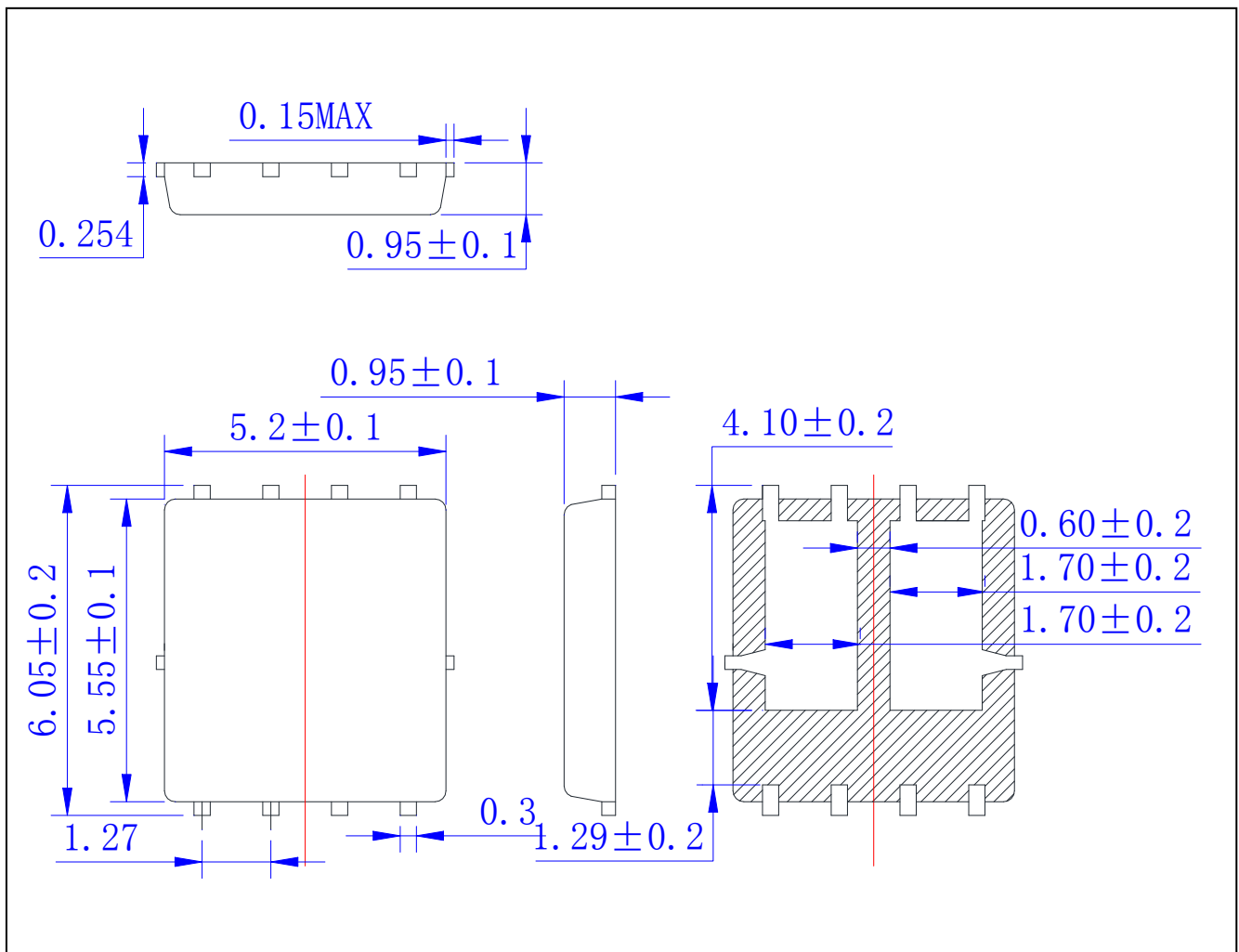


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



DFN5×6 OUTLINE



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